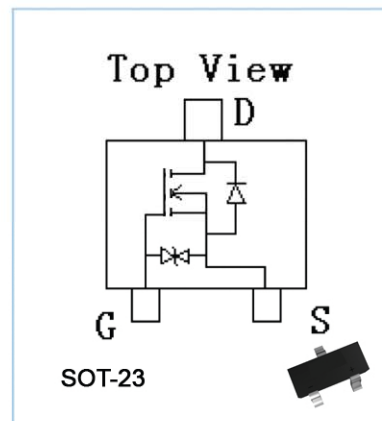


## N-Channel Enhancement Mode MOSFET Feature

- 60V / 0.5A,  $R_{DS(ON)} = 2.5 \Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} = 2.5 \Omega @ V_{GS} = 4.5V$
- SOT-23 for Surface Mount Package.

### Applications

- Direct Logic-level Interface: TTL/CMOS.
- Drivers: Relays, Lamps, Display, Transister, etc.
- Battery Operated Systems.



### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	0.5	A

### Electrical Characteristics

$T_A = 25^\circ\text{C}$  Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS} = 0V, I_D = 10\mu A$	60	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate Body Leakage Current, Forward	IGSSF	$V_{GS} = 20V, V_{DS} = 0V$	-	-	10	$\mu A$
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS} = -20V, V_{DS} = 0V$	-	-	-10	$\mu A$
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1	-	1.3	V
Static Drain-source On-Resistance	RDS(ON)	$V_{GS} = 10V, I_D = 0.5A$	-	-	2.5	$\Omega$
		$V_{GS} = 4.5V, I_D = 0.2A$	-	-	2.5	$\Omega$
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	VSD	$V_{GS} = 0V, I_S = 0.2A$			2.5	V

